## LECTURE -22

BIT ->> 2 TYPES

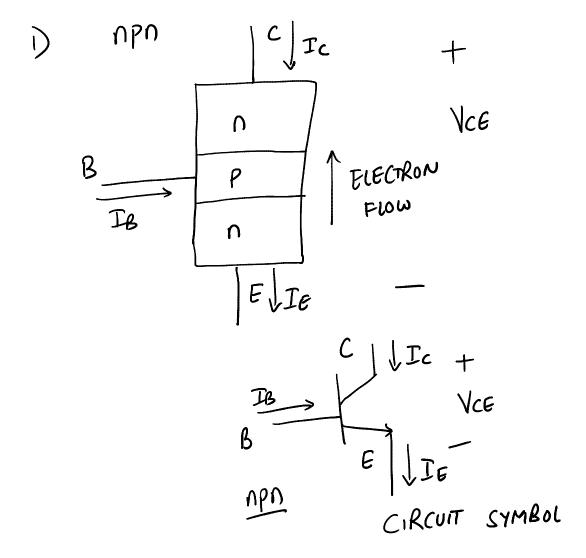
- D PTYPE MATERIAL BETWEEN TWO N-TYPE
  MATERIALS NPN
- 2) NTYPE MATERIAL BETWEEN TWO P-TYPE MATERIALS POP

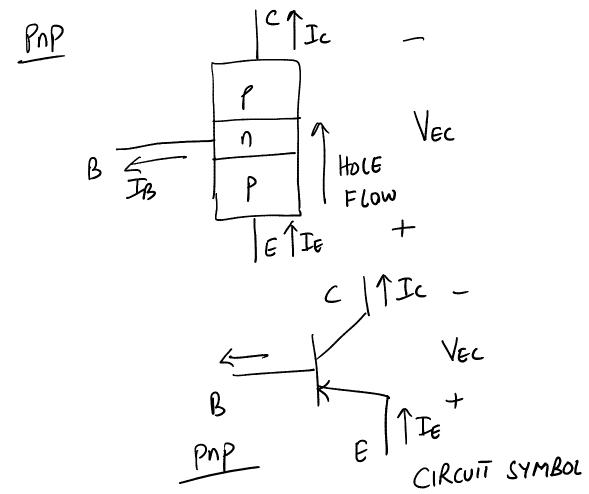
3-TERMINAL DEVICE

BASE (B)

COLLE CTUR (4)

EMITTER (E)

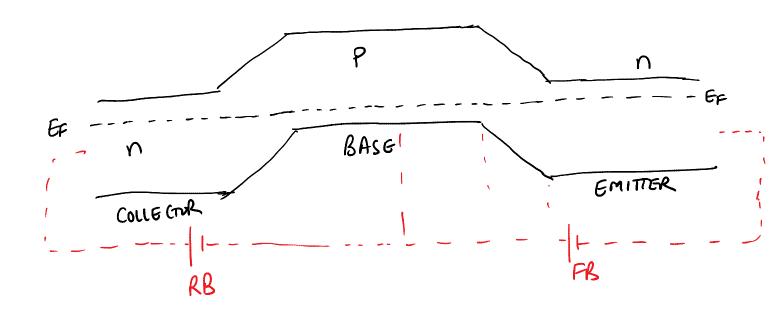




## BJT OPERATING CONDITIONS ACTIVE BASE EMITTER JUNCTION -> FORWARD BIASED COLLECTOR BASE JUNCTION -> REVERSE

NPN AT ESUILIBRIUM

npn



## FB EB JUNCTION

- ( ) JUNCTION WIDTH NARROWES
- (2) DIFFUSION CURRENT DOMINATES
- 3) HOLES INTECTED TO INTO EMITTER EX
- (4) ELECTRONS INTECTED INTO BAKE REGION

## RB CB TUNCTION

- (I) JUNCTION & WIDTH INCREASES
- 3 PRIFT CURRENT DOMINATES
- 3) ELECTRONS ARE EXTRACTED FROM COLLECTOR REGION
- 4) HOLES ARE EXTRACTED FROM BASE REGION